

Technical Data of AZ TFP-650

Ref. AZ TFP-650F5

=Process Margin=

1. Pre-bake Temperature Dependence
2. Development Time Dependence



Process Margin_Prebake Temp.& Dev. Time

Process Condition

Substrate: Bare Si

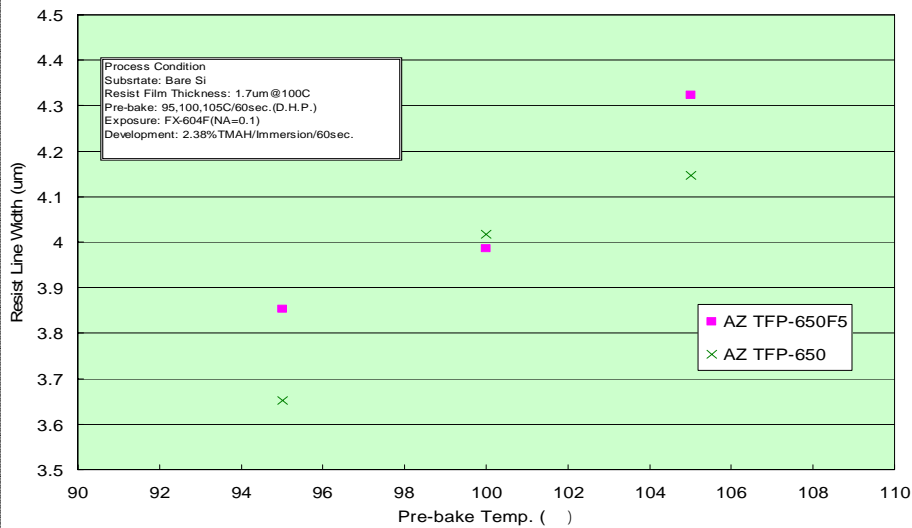
Resist Film Thickness: 1.7um@100C

Pre-bake: 95,100,105C/60sec.

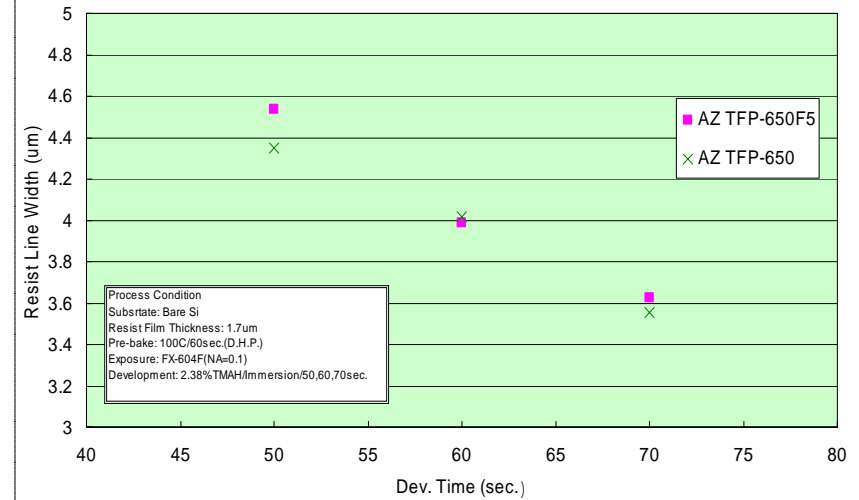
Exposure: Nikon FX-604F (NA=0.1)

Development: 2.38%TMAH/Immersion/50,60,70sec.

Pre-bake Temp. Dependence

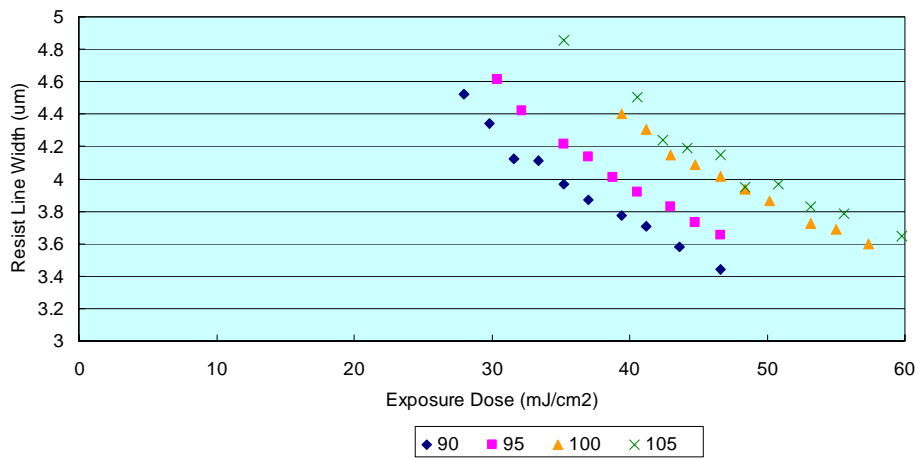


Dev. Time Dependence

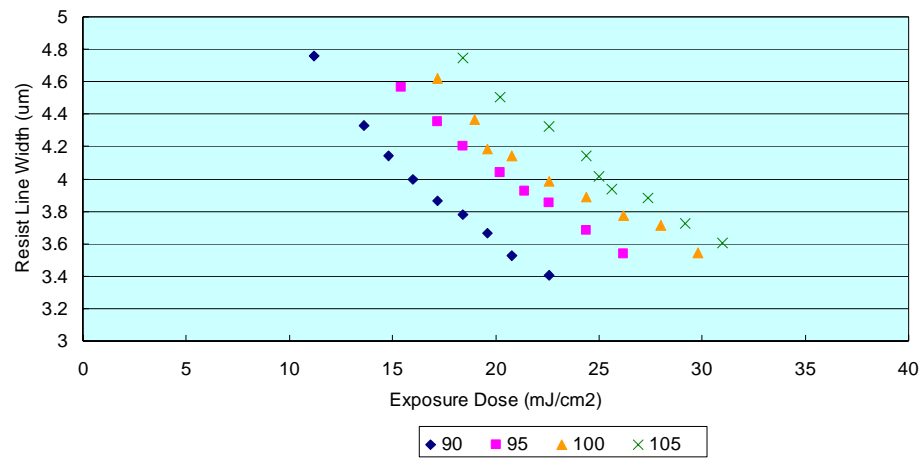


CD curve_Prebake Temp. Dependence

**Pre-bake Temp. Dependence of
AZ TFP-650**



**Pre-bake Temp. Dependence of
AZ TFP-650F5**



AZ TFP-650

Pre-bake Temp.(C)	Initial F.T.(A)	Remaining F.T.(A)	N.F.T.(%)	Eo (mJ/cm2)
90	17355	16971	97.79	35.2
95	17233	16952	98.36941	38.8
100	16978	16782	98.84556	46.6
105	16893	16802	99.46132	48.4

AZ TFP-650F5

Pre-bake Temp.(C)	Initial F.T.(A)	Remaining F.T.(A)	N.F.T.(%)	Eo (mJ/cm2)
90	17412	13782	79.15	16
95	17258	14737	85.39	20.2
100	17010	15232	89.55	22.6
105	16930	16163	95.47	25

